

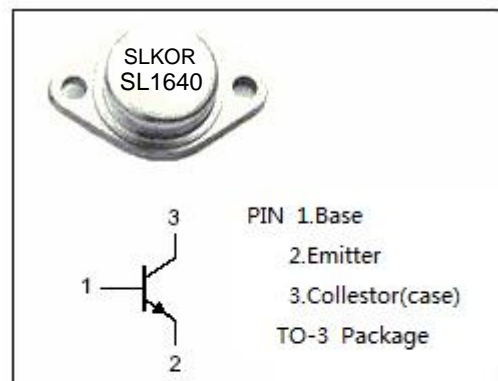
## Silicon NPN Power Transistor

### DESCRIPTION

- Excellent Safe Operating Area
- High DC Current Gain- $h_{FE}=60(\text{Min})@I_C = 4A$
- Low Saturation Voltage-  
:  $V_{CE(\text{sat})}= 1.4V(\text{Max})@ I_C = 8A$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation.

### APPLICATIONS

- Designed for high power audio ,disk head positioners and other linear applications, which can also be used in power switching circuits such as relay or solenoid drivers, DC-DC converters or inverters.

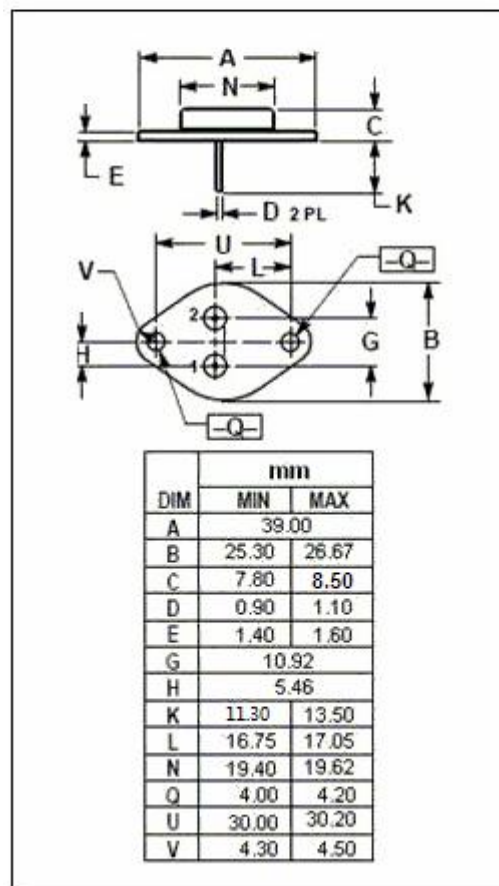


### ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	400	V
$V_{CEO}$	Collector-Emitter Voltage	250	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	16	A
$I_B$	Base Current-Continuous	4	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	200	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-65~150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	0.83	$^\circ\text{C}/\text{W}$



**ELECTRICAL CHARACTERISTICS**
 **$T_C=25^{\circ}\text{C}$  unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=30\text{mA}$ ; $I_B=0$	250		V
$V_{CBO}$	Collector- Base Voltage	$I_C=1\text{mA}$ ; $I_E=0$	400		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C= 8\text{A}$ ; $I_B= 0.8\text{A}$		1.4	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C= 16\text{A}$ ; $I_B= 3.2\text{A}$		4.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C= 8\text{A}$ ; $V_{CE}= 4\text{V}$		2.2	V
$I_{CEO}$	Collector Cutoff Current	$V_{CE}= 250\text{V}$ ; $I_B=0$		1	mA
$I_{CBO}$	Collector Cutoff Current	$V_{CE}= 400\text{V}$ ; $I_B=0$		0.1	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}= 5\text{V}$ ; $I_C=0$		1	mA
$h_{FE-1}$	DC Current Gain	$I_C=0.2\text{A}$ ; $V_{CE}= 4\text{V}$	40		
$h_{FE-2}$	DC Current Gain	$I_C=0.5\text{A}$ ; $V_{CE}= 4\text{V}$	40		
$h_{FE-3}$	DC Current Gain	$I_C=1\text{A}$ ; $V_{CE}= 4\text{V}$	60	120	
$h_{FE-4}$	DC Current Gain	$I_C=4\text{A}$ ; $V_{CE}= 4\text{V}$	60	100	

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